

SKiiP 03AC126V1



MiniSKiiP[®]0

3-phase bridge inverter

SKiiP 03 AC 126 V1

Preliminary Data

Features

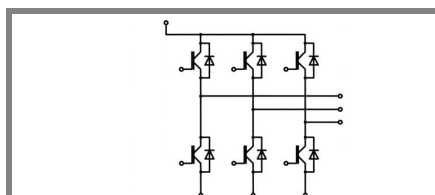
- Fast Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Remarks

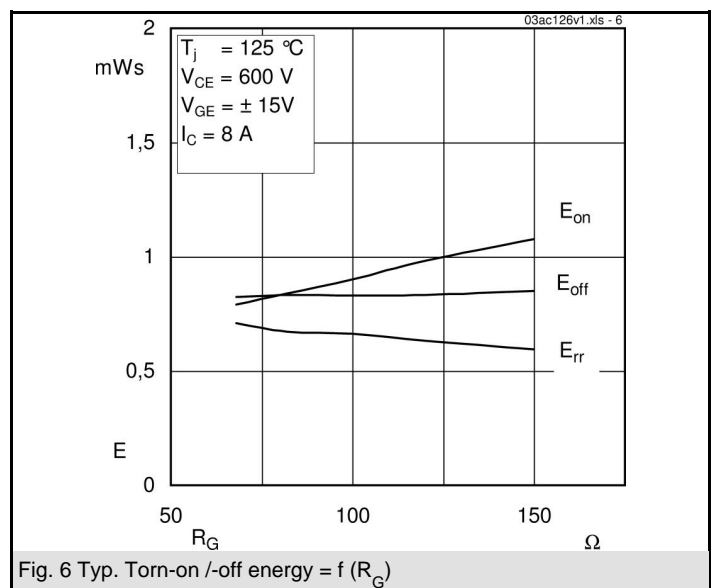
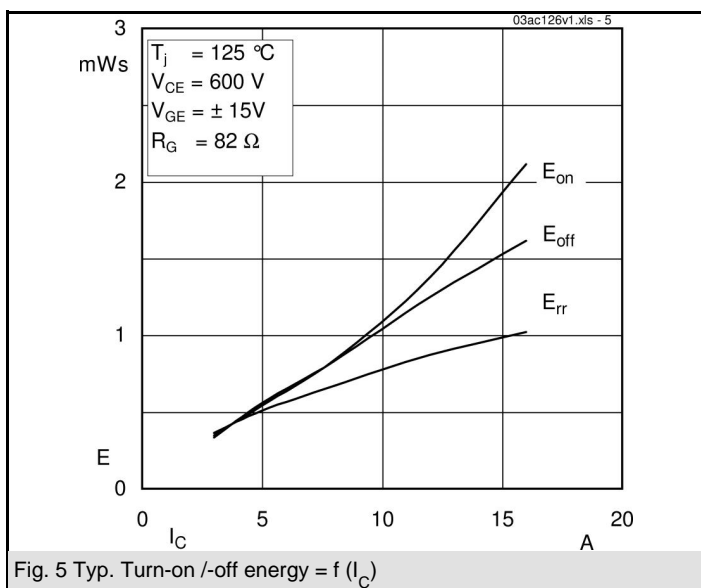
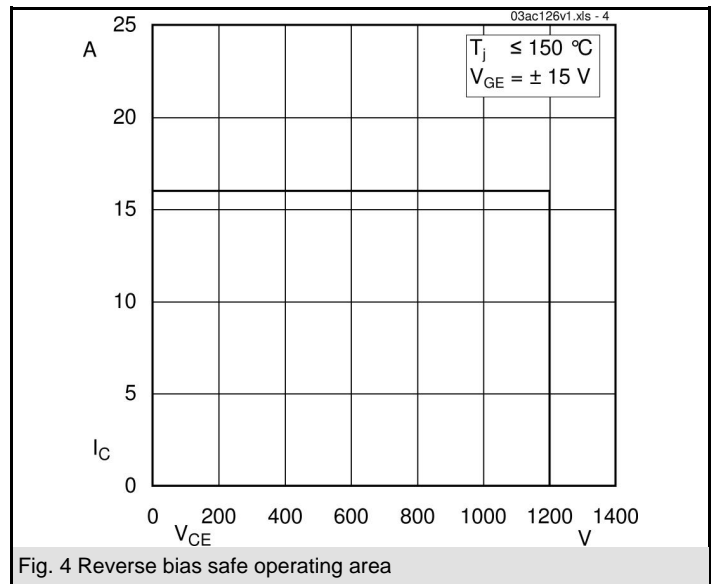
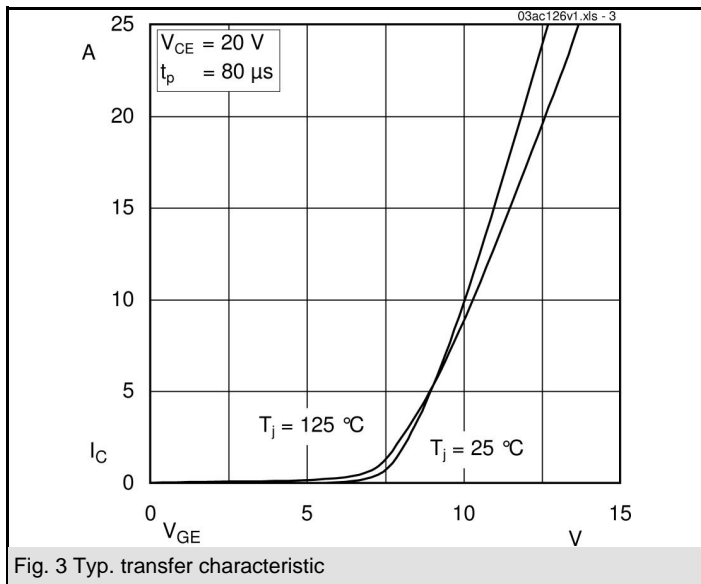
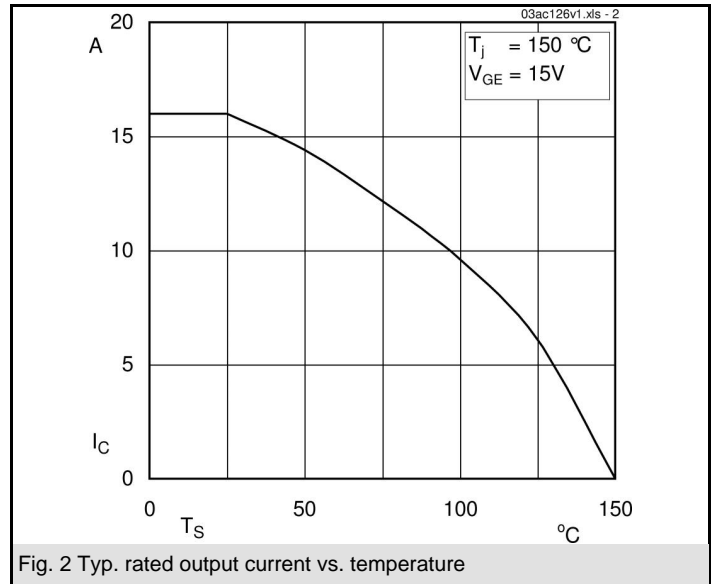
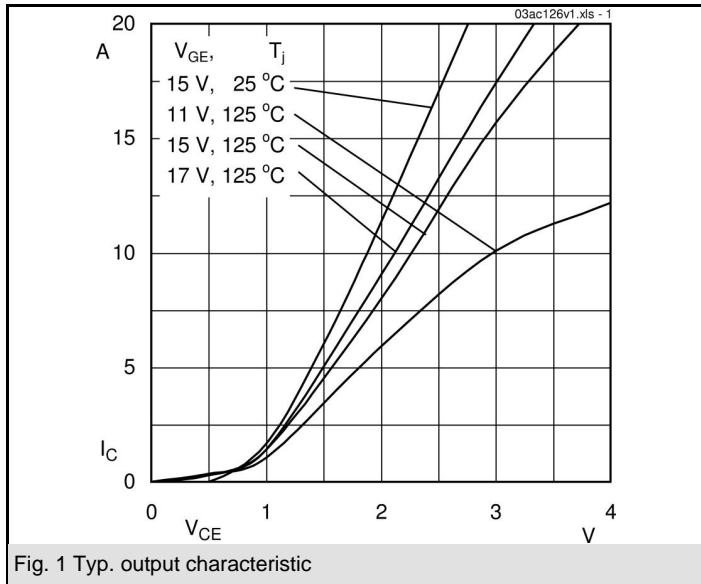
- V_{CEsat} , V_F = chip level value
- without T-Sensor

Absolute Maximum Ratings		$T_S = 25\text{ °C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT - Inverter			
V_{CES}	$T_S = 25\text{ (70) °C}$ $t_p \leq 1\text{ ms}$	1200	V
I_C		16 (15)	A
I_{CRM}		16	A
V_{GES}		± 20	V
T_j		-40...+150	°C
Diode - Inverter			
I_F	$T_S = 25\text{ (70) °C}$ $t_p \leq 1\text{ ms}$	14 (11)	A
I_{FRM}		16	A
T_j		-40...+150	°C
I_{tRMS}	per power terminal (20 A / spring)	20	A
T_{stg}	$T_{op} \leq T_{stg}$	-40...+125	°C
V_{isol}	AC, 1 min.	2500	V

Characteristics		$T_S = 25\text{ °C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT - Inverter					
V_{CEsat}	$I_{Cnom} = 8\text{ A}$, $T_j = 25\text{ (125) °C}$		1,7 (2)	2,1 (2,4)	V
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 0,3\text{ mA}$	5	5,8	6,5	V
$V_{CE(TO)}$	$T_j = 25\text{ (125) °C}$		1 (0,9)	1,2 (1,1)	V
r_T	$T_j = 25\text{ (125) °C}$		87 (138)	113 (162)	mΩ
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		0,7		nF
C_{oes}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		0,1		nF
C_{res}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		0,1		nF
$R_{th(j-s)}$	per IGBT		1,5		K/W
$t_{d(on)}$	under following conditions		40		ns
t_r	$V_{CC} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$		25		ns
$t_{d(off)}$	$I_{Cnom} = 8\text{ A}$, $T_j = 125\text{ °C}$		370		ns
t_f	$R_{Gon} = R_{Goff} = 82\text{ Ω}$		85		ns
E_{on}	inductive load		0,9		mJ
E_{off}			0,9		mJ
Diode - Inverter					
$V_F = V_{EC}$	$I_{Fnom} = 8\text{ A}$, $T_j = 25\text{ (125) °C}$		1,9 (2)	2,2 (2,4)	V
$V_{(TO)}$	$T_j = 25\text{ (125) °C}$		1 (0,8)	1,1 (0,9)	V
r_T	$T_j = 25\text{ (125) °C}$		112 (150)	138 (187)	mΩ
$R_{th(j-s)}$	per diode		2,5		K/W
I_{RRM}	under following conditions		13		A
Q_{rr}	$I_{Fnom} = 8\text{ A}$, $V_R = 600\text{ V}$		1,6		μC
E_{rr}	$V_{GE} = 0\text{ V}$, $T_j = 125\text{ °C}$ $di_F/dt = 480\text{ A/μs}$		0,7		mJ
Temperature Sensor					
R_{ts}	%, $T_r = (\text{) °C}$		()		Ω
Mechanical Data					
m			21,5		g
M_s	Mounting torque	2		2,5	Nm



AC



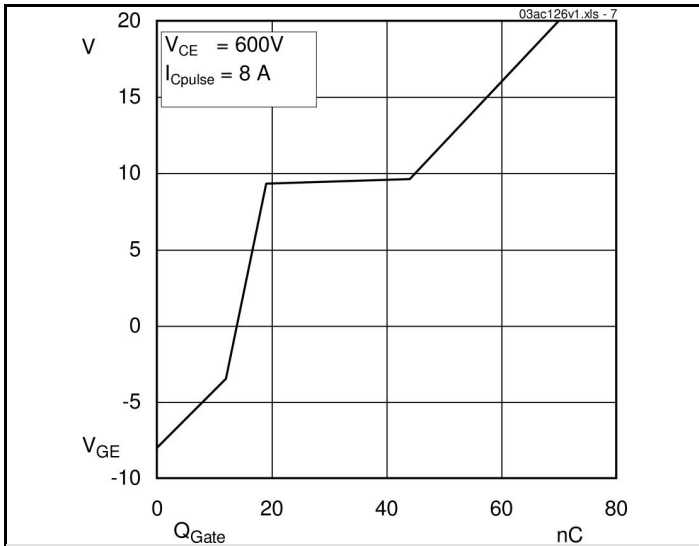


Fig. 7 Typ. gate charge characteristic

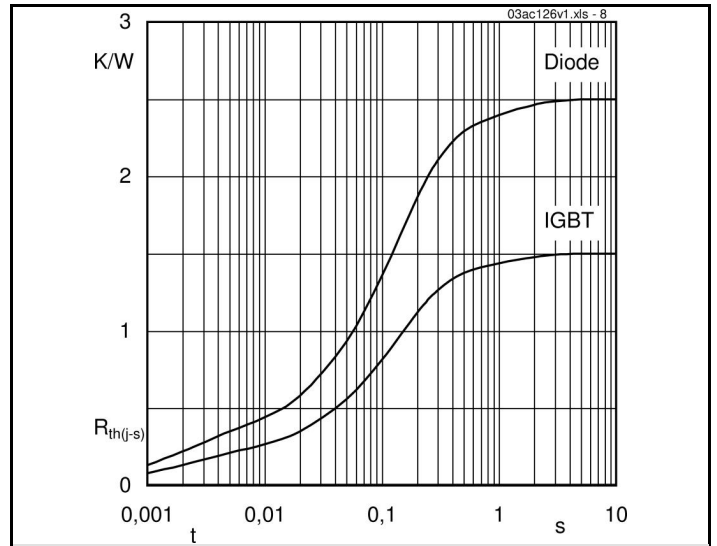


Fig. 8 Typ. thermal impedance

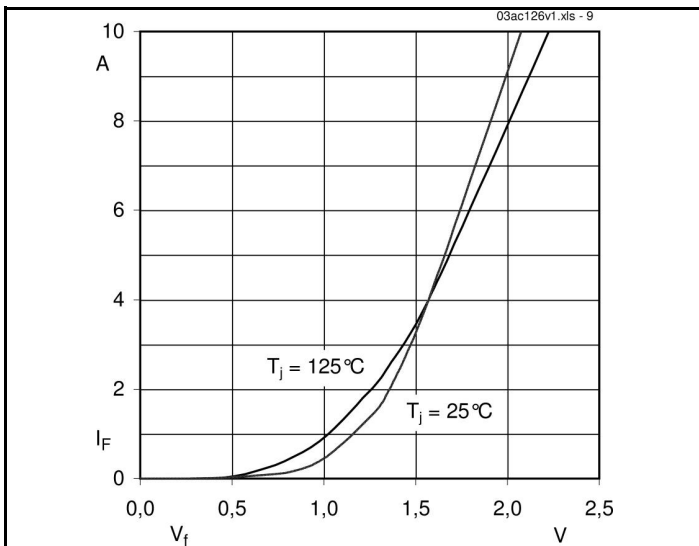
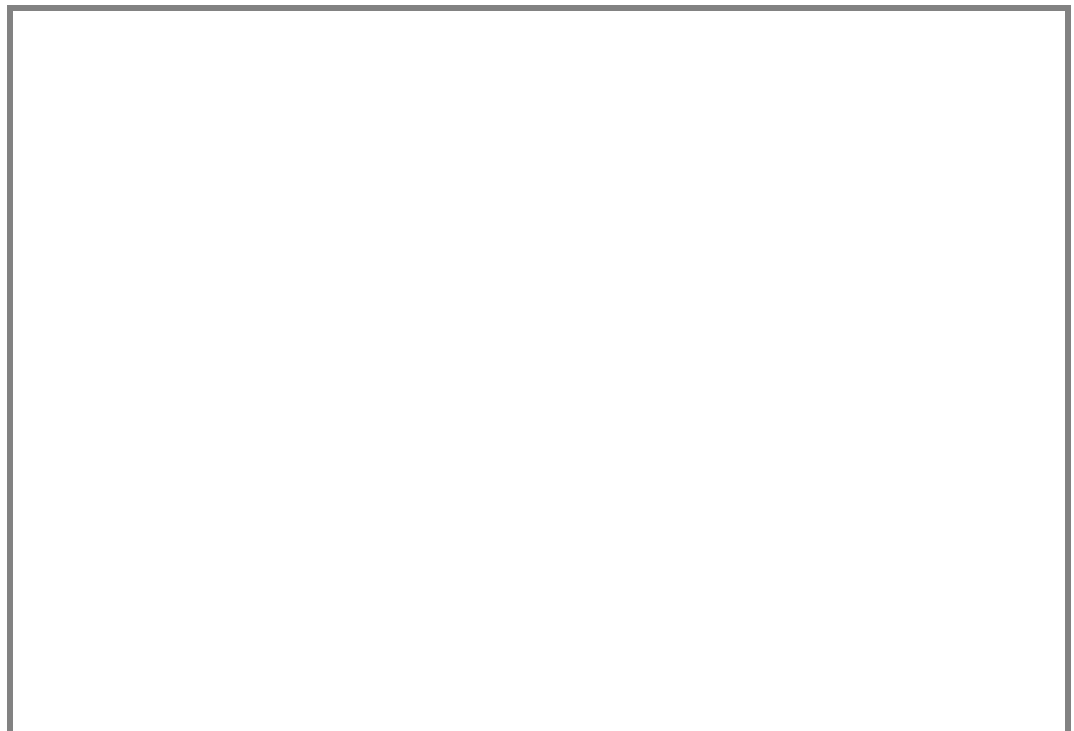
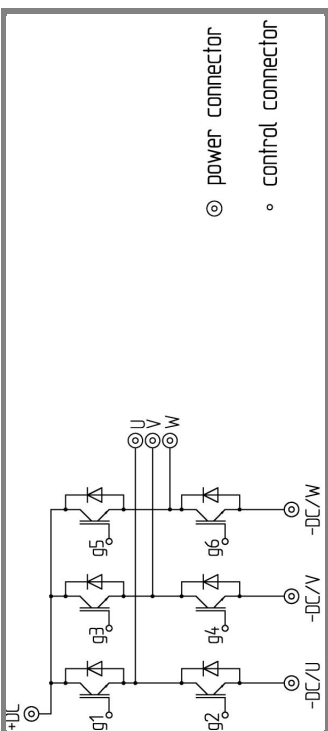
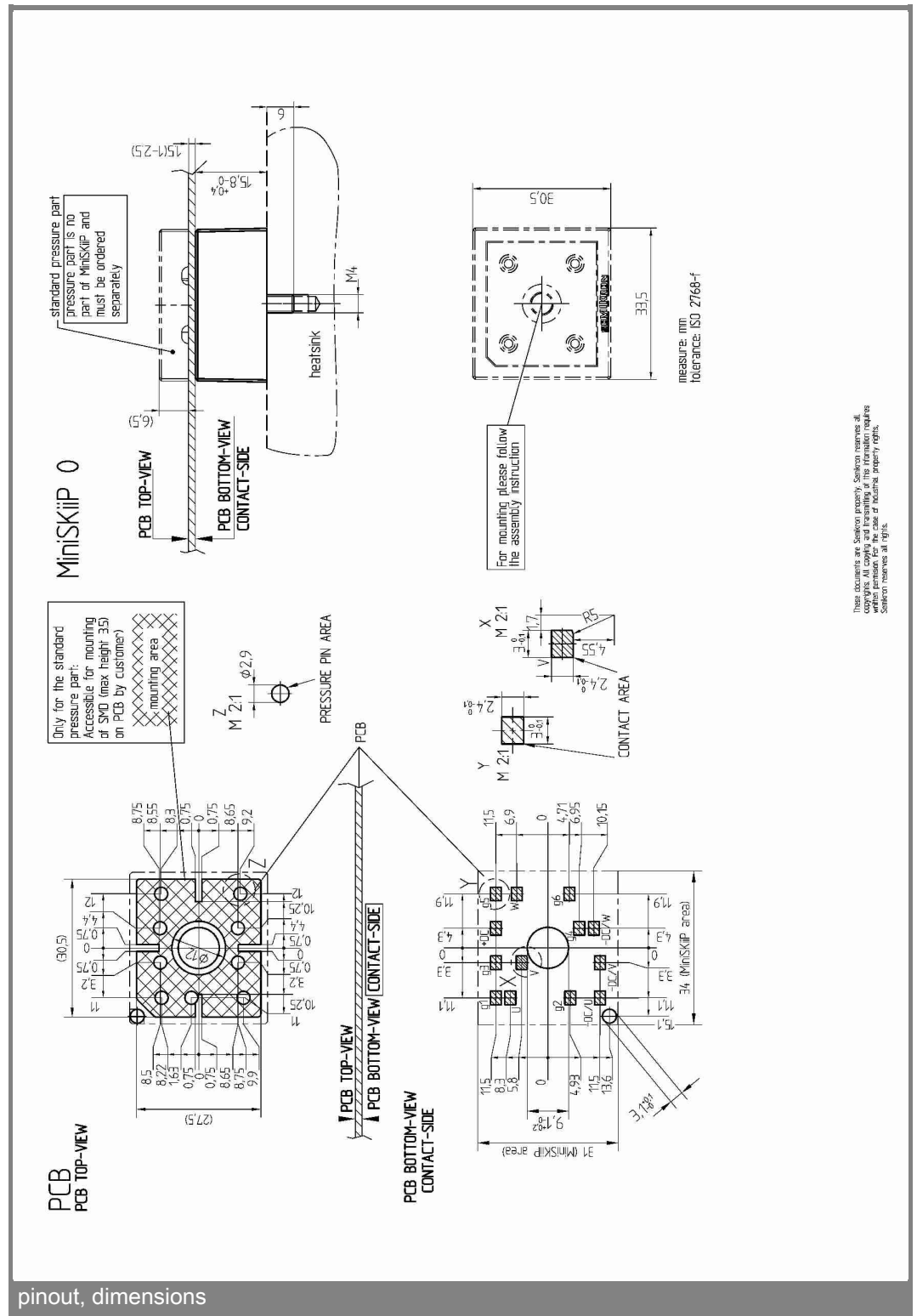


Fig. 9 Typ. freewheeling diode forward characteristic





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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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